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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	25MHz
Connectivity	I²C, IrDA, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I²S, POR, PWM, WDT
Number of I/O	37
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.98V ~ 3.8V
Data Converters	A/D 4x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-TQFP
Supplier Device Package	48-TQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32hg222f32g-a-qfp48

Module	Configuration	Pin Connections
IDAC0	Full configuration	IDAC0_OUT
AES	Full configuration	NA
GPIO	37 pins	Available pins are shown in Table 4.3 (p. 56)

2.3 Memory Map

The *EFM32HG222* memory map is shown in Figure 2.2 (p. 7), with RAM and Flash sizes for the largest memory configuration.

Figure 2.2. EFM32HG222 Memory Map with largest RAM and Flash sizes

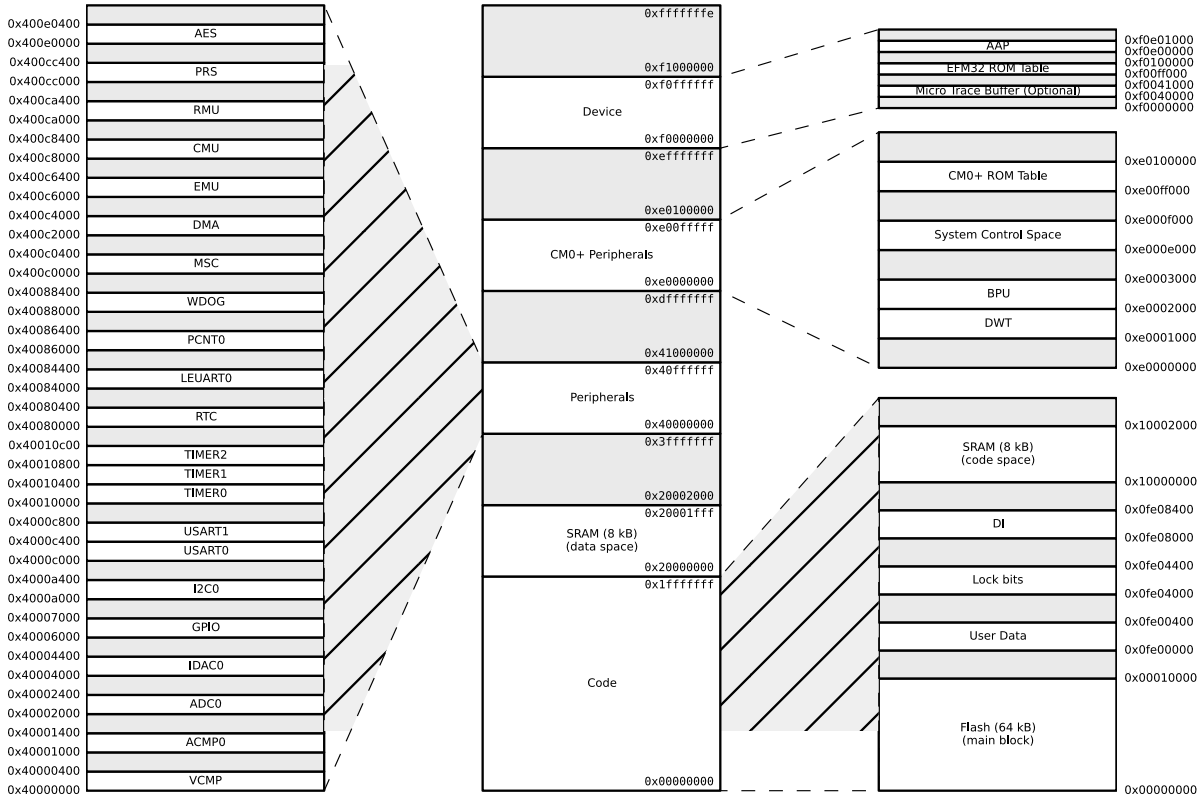


Figure 3.7. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 21 MHz

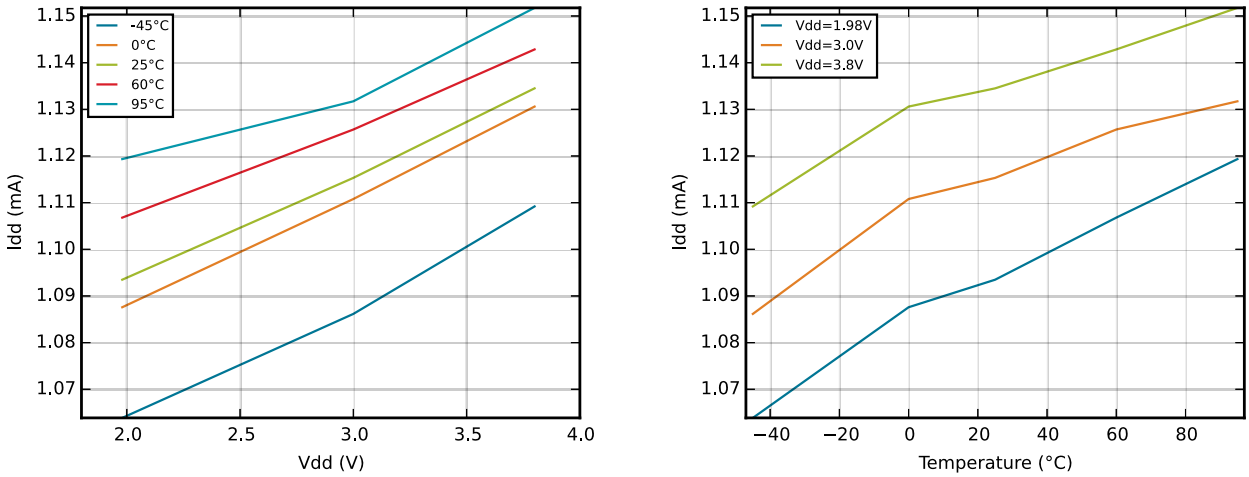
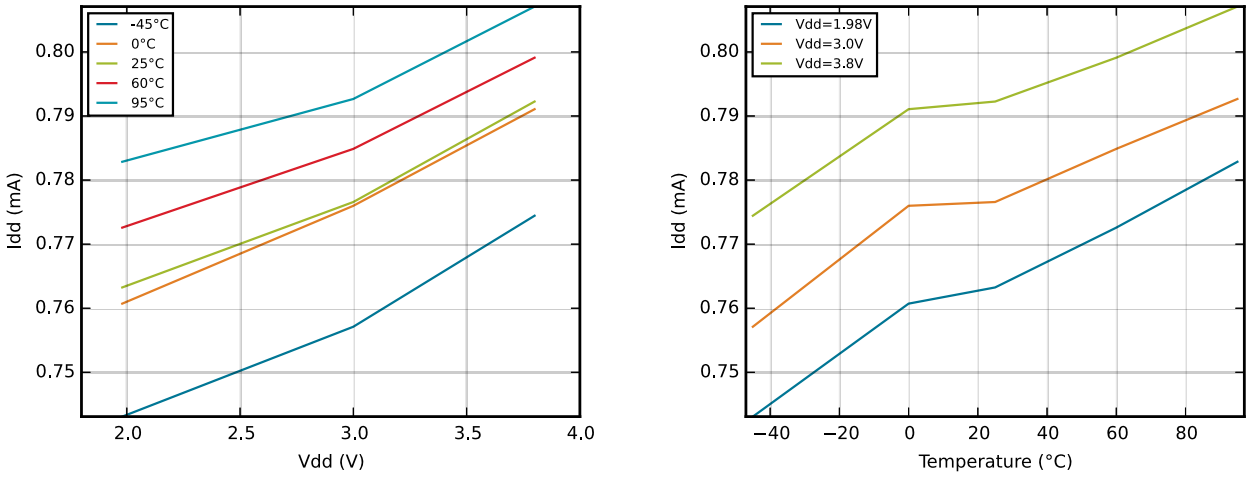
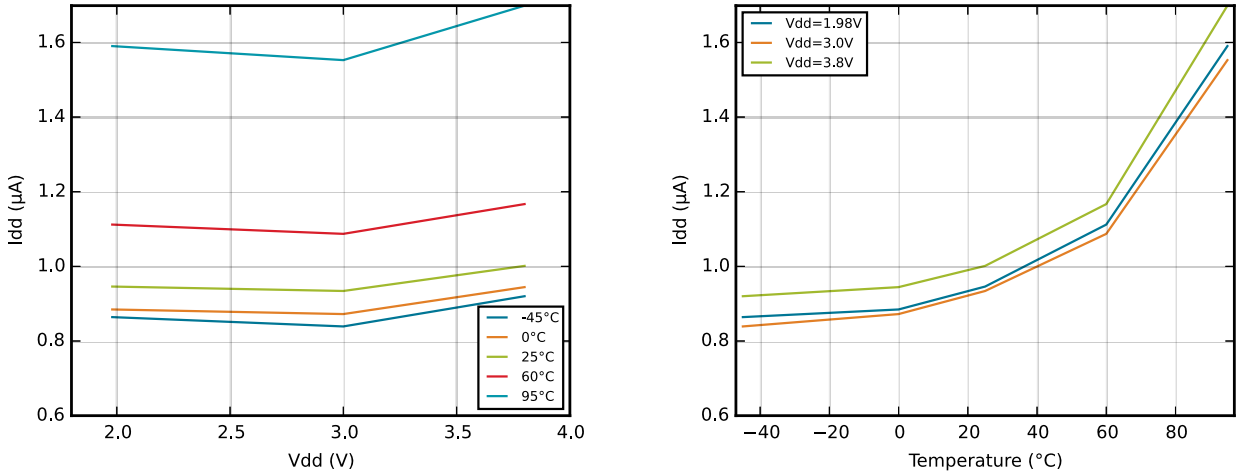


Figure 3.8. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 14 MHz



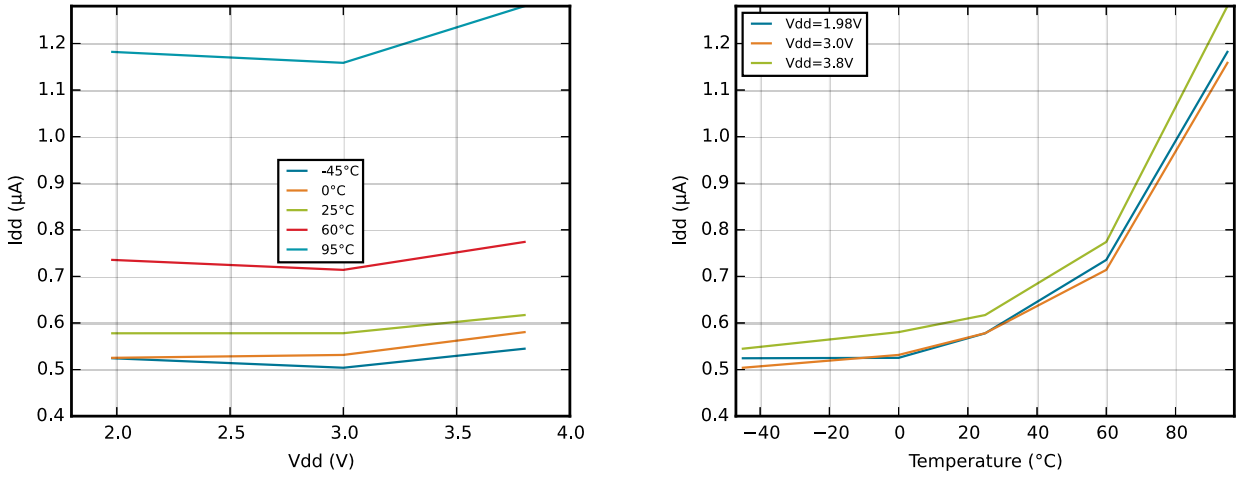
3.4.3 EM2 Current Consumption

Figure 3.11. EM2 current consumption. RTC prescaled to 1kHz, 32.768 kHz LFRCO.



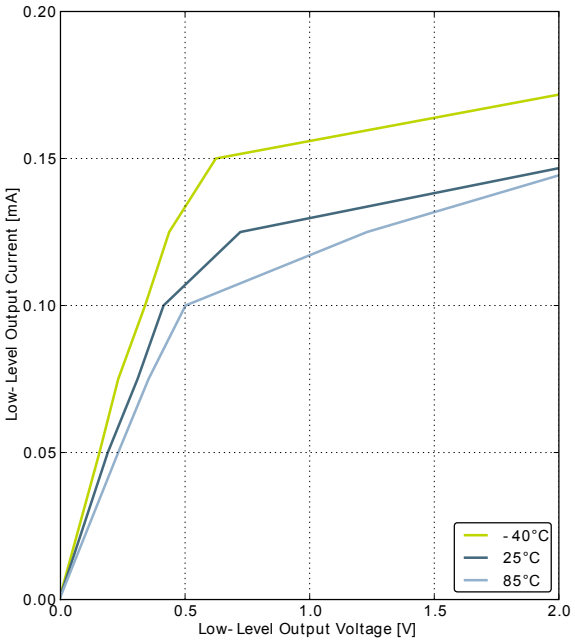
3.4.4 EM3 Current Consumption

Figure 3.12. EM3 current consumption.

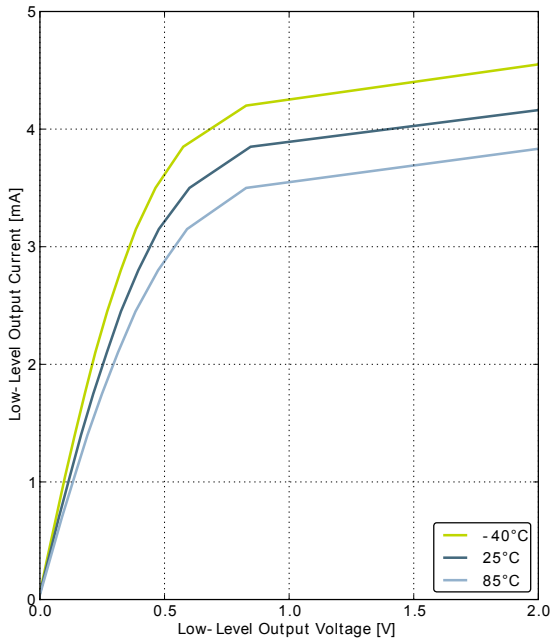


Symbol	Parameter	Condition	Min	Typ	Max	Unit
		Sourcing 1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.85V_{DD}		V
		Sourcing 1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.90V_{DD}		V
		Sourcing 6 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	0.75V_{DD}			V
		Sourcing 6 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	0.85V_{DD}			V
		Sourcing 20 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH	0.60V_{DD}			V
		Sourcing 20 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = HIGH	0.80V_{DD}			V
V_{IOOL}	Output low voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sinking 0.1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.20V_{DD}		V
		Sinking 0.1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.10V_{DD}		V
		Sinking 1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.10V_{DD}		V
		Sinking 1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.05V_{DD}		V
		Sinking 6 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			0.30V_{DD}	V
		Sinking 6 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			0.20V_{DD}	V
		Sinking 20 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH			0.35V_{DD}	V
		Sinking 20 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = HIGH			0.25V_{DD}	V
I_{IOLEAK}	Input leakage current	High Impedance IO connected to GROUND or Vdd		±0.1	±40	nA
R_{PU}	I/O pin pull-up resistor			40		kOhm
R_{PD}	I/O pin pull-down resistor			40		kOhm
R_{IOESD}	Internal ESD series resistor			200		Ohm
$t_{IOGLITCH}$	Pulse width of pulses to be removed		10		50	ns

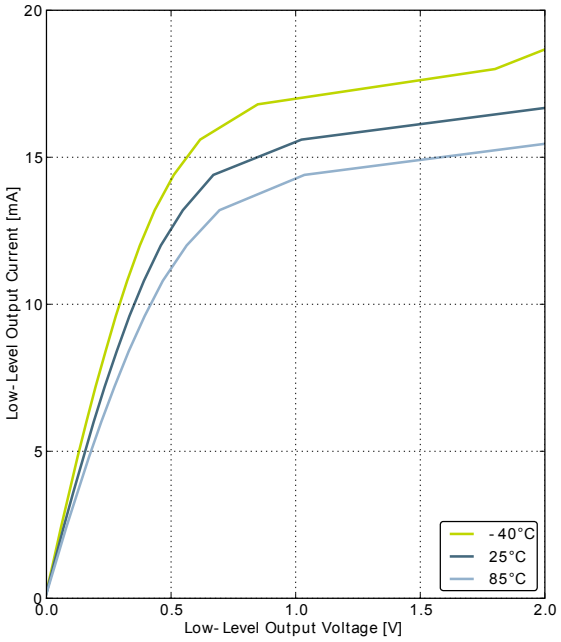
Figure 3.14. Typical Low-Level Output Current, 2V Supply Voltage



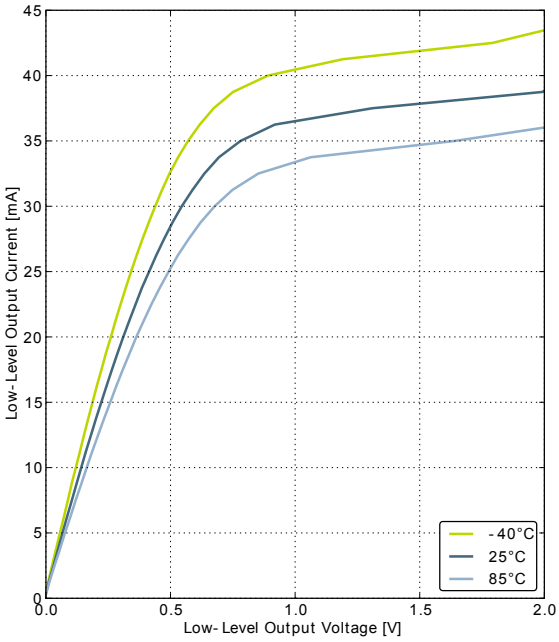
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = LOW

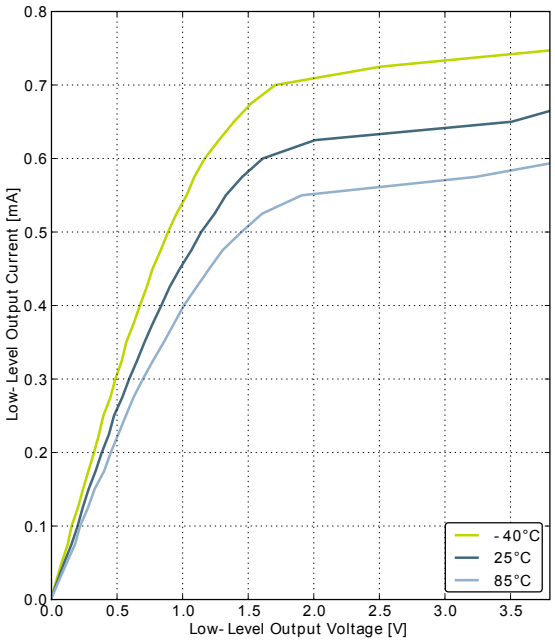


GPIO_Px_CTRL DRIVEMODE = STANDARD

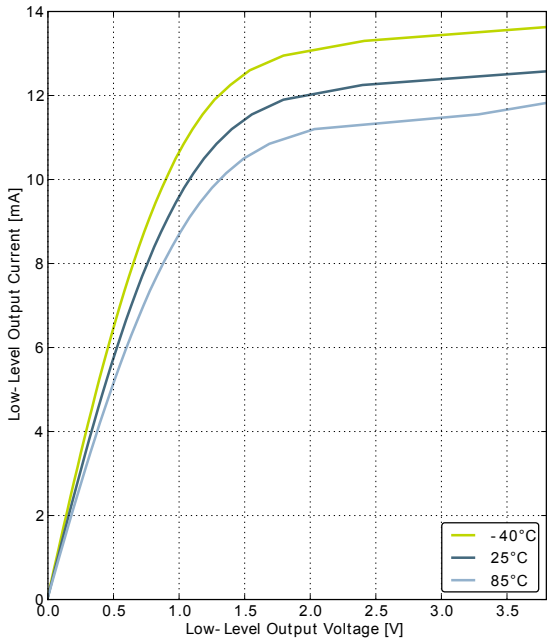


GPIO_Px_CTRL DRIVEMODE = HIGH

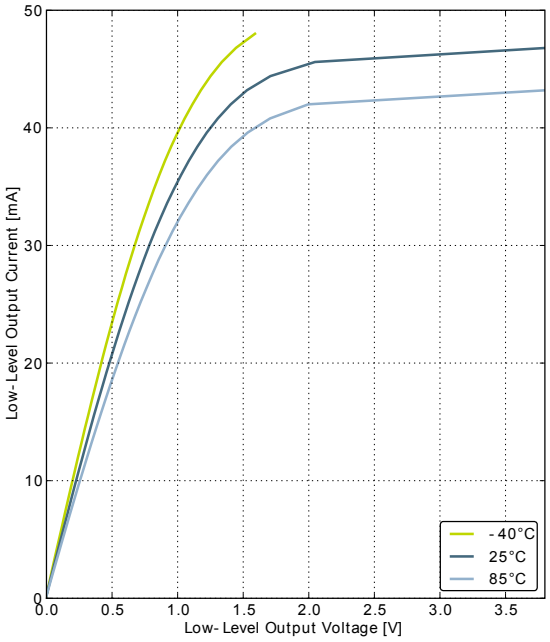
Figure 3.18. Typical Low-Level Output Current, 3.8V Supply Voltage



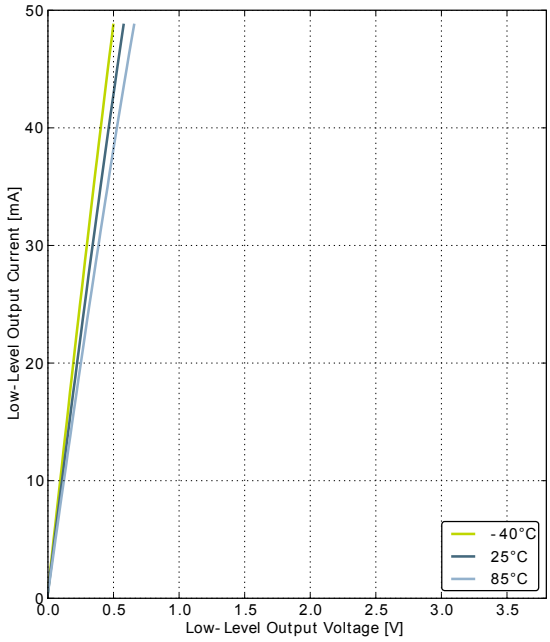
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = LOW

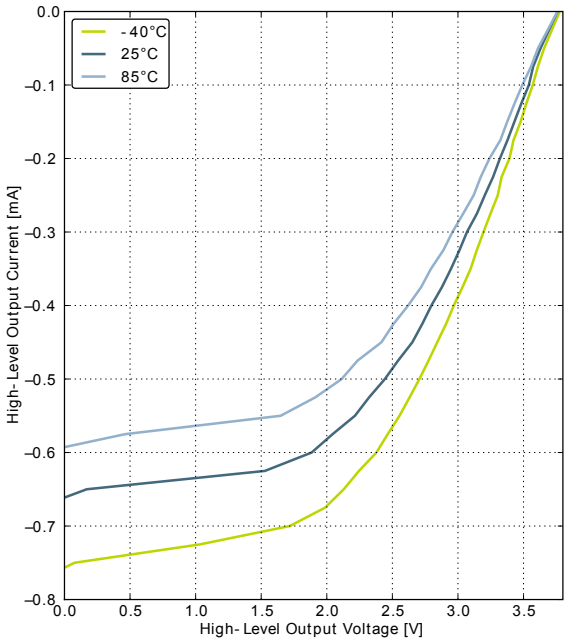


GPIO_Px_CTRL DRIVEMODE = STANDARD

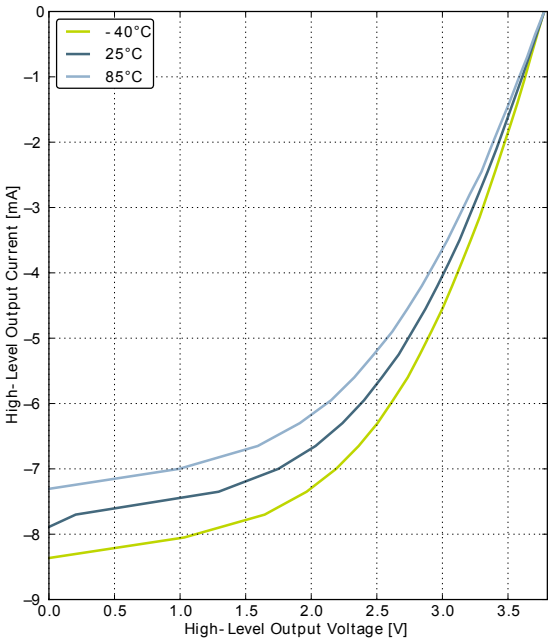


GPIO_Px_CTRL DRIVEMODE = HIGH

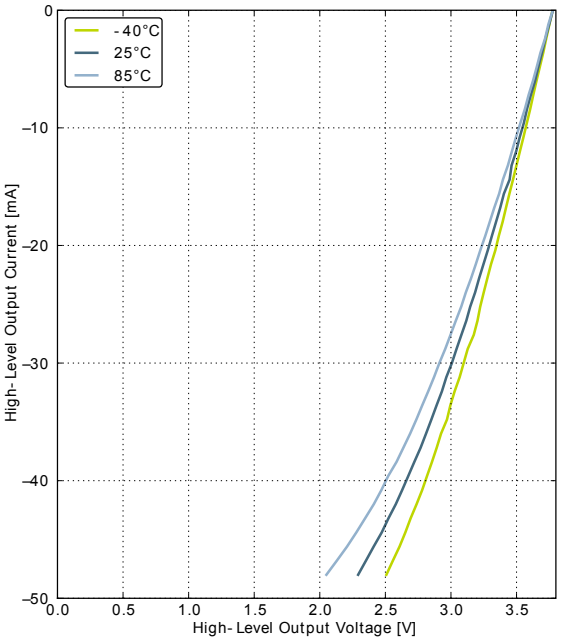
Figure 3.19. Typical High-Level Output Current, 3.8V Supply Voltage



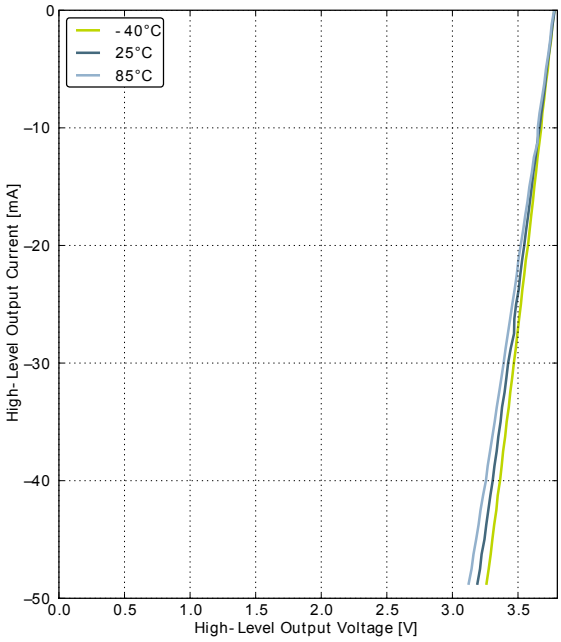
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = STANDARD



GPIO_Px_CTRL DRIVEMODE = HIGH

3.9 Oscillators

3.9.1 LFXO

Table 3.8. LFXO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{LFXO}	Supported nominal crystal frequency			32.768		kHz
ESR_{LFXO}	Supported crystal equivalent series resistance (ESR)			30	120	kOhm
C_{LFXOL}	Supported crystal external load range		5		25	pF
I_{LFXO}	Current consumption for core and buffer after startup.	ESR=30 kOhm, C_L=10 pF, LFXOBOOST in CMU_CTRL is 1		190		nA
t_{LFXO}	Start- up time.	ESR=30 kOhm, C_L=10 pF, 40% - 60% duty cycle has been reached, LFXOBOOST in CMU_CTRL is 1		1100		ms

For safe startup of a given crystal, the Configurator tool in Simplicity Studio contains a tool to help users configure both load capacitance and software settings for using the LFXO. For details regarding the crystal configuration, the reader is referred to application note "AN0016 EFM32 Oscillator Design Consideration".

3.9.2 HFXO

Table 3.9. HFXO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{HFXO}	Supported frequency, any mode		4		25	MHz
ESR_{HFXO}	Supported crystal equivalent series resistance (ESR)	Crystal frequency 25 MHz		30	100	Ohm
		Crystal frequency 4 MHz		400	1500	Ohm
g_{mHFXO}	The transconductance of the HFXO input transistor at crystal startup	HFXOBOOST in CMU_CTRL equals 0b11	20			mS
C_{HFXOL}	Supported crystal external load range		5		25	pF
I_{HFXO}	Current consumption for HFXO after startup	4 MHz: ESR=400 Ohm, C_L=20 pF, HFXOBOOST in CMU_CTRL equals 0b11		85		µA
		25 MHz: ESR=30 Ohm, C_L=10 pF, HFXOBOOST in CMU_CTRL equals 0b11		165		µA
t_{HFXO}	Startup time	25 MHz: ESR=30 Ohm, C_L=10 pF, HFXOBOOST in CMU_CTRL equals 0b11		785		µs

Figure 3.22. Calibrated HFRCO 7 MHz Band Frequency vs Supply Voltage and Temperature

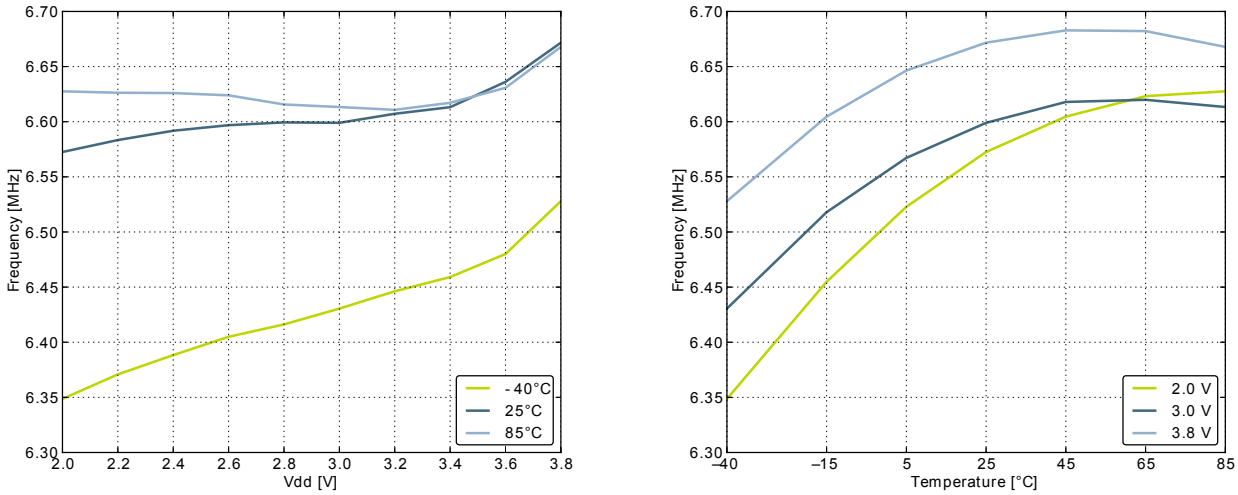


Figure 3.23. Calibrated HFRCO 11 MHz Band Frequency vs Supply Voltage and Temperature

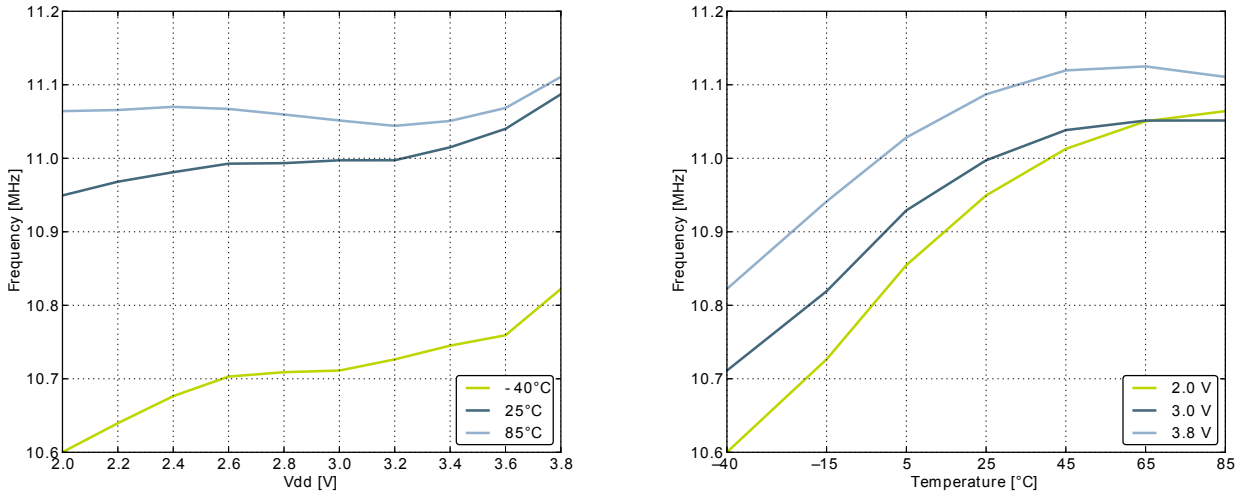
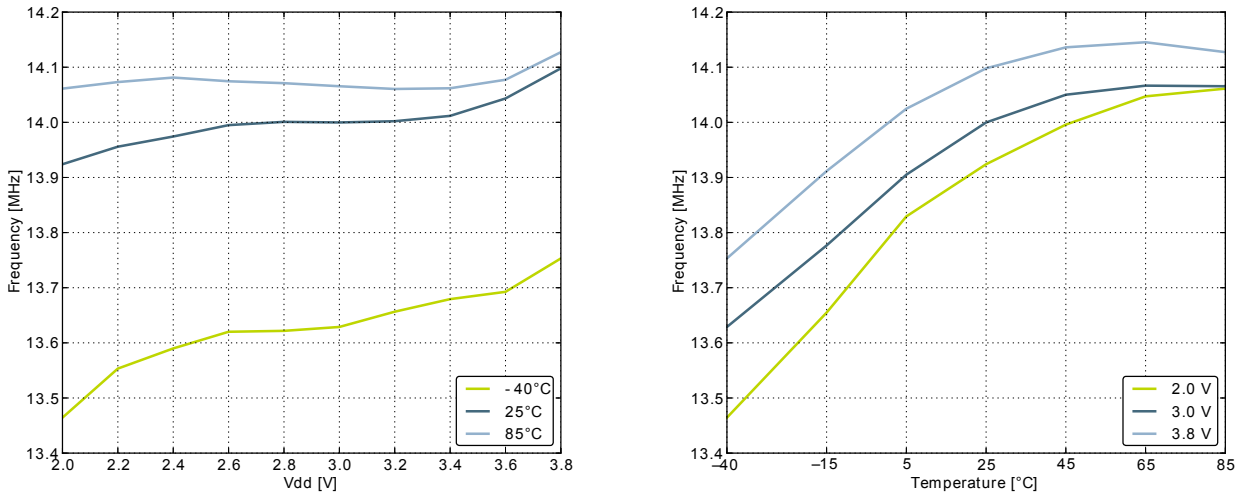


Figure 3.24. Calibrated HFRCO 14 MHz Band Frequency vs Supply Voltage and Temperature



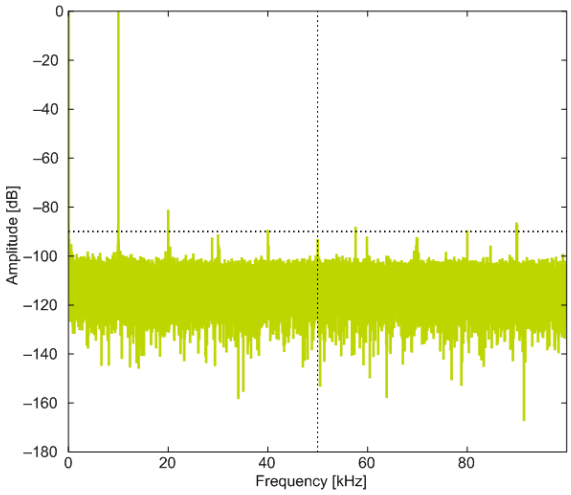
Symbol	Parameter	Condition	Min	Typ	Max	Unit
		200 kSamples/s, 12 bit, single ended, V_{DD} reference		76		dBc
		200 kSamples/s, 12 bit, differential, internal 1.25V reference		79		dBc
		200 kSamples/s, 12 bit, differential, internal 2.5V reference		79		dBc
		200 kSamples/s, 12 bit, differential, 5V reference		78		dBc
		200 kSamples/s, 12 bit, differential, V_{DD} reference	68	79		dBc
		200 kSamples/s, 12 bit, differential, 2xV_{DD} reference		79		dBc
$V_{ADCOFFSET}$	Offset voltage	After calibration, single ended	-4	0.3	4	mV
		After calibration, differential		0.3		mV
$TGRAD_{ADCTH}$	Thermometer output gradient			-1.92		mV/°C
				-6.3		ADC Codes/ °C
DNL_{ADC}	Differential non-linearity (DNL)	V_{DD}= 3.0 V, external 2.5V reference	-1	±0.7	4	LSB
INL_{ADC}	Integral non-linearity (INL), End point method			±1.6	±3	LSB
MC_{ADC}	No missing codes		11.999[1]	12		bits
$VREF_{ADC}$	ADC Internal Voltage Reference	Internal 1.25V, V_{DD} = 3V, 25°C	1.248	1.254	1.262	V
		Internal 1.25V, Full temperature and supply range	1.188	1.254	1.302	V
		Internal 2.5V, V_{DD} = 3V, 25°C	2.492	2.506	2.520	V
		Internal 2.5V, Full temperature and supply range	2.402	2.506	2.600	V

[1]On the average every ADC will have one missing code, most likely to appear around 2048 ± n*512 where n can be a value in the set {-3, -2, -1, 1, 2, 3}. There will be no missing code around 2048, and in spite of the missing code the ADC will be monotonic at all times so that a response to a slowly increasing input will always be a slowly increasing output. Around the one code that is missing, the neighbour codes will look wider in the DNL plot. The spectra will show spurs on the level of -78dBc for a full scale input for chips that have the missing code issue.

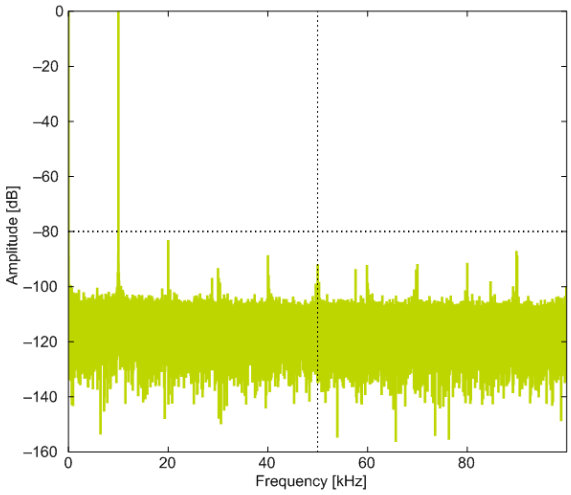
The integral non-linearity (INL) and differential non-linearity parameters are explained in Figure 3.26 (p. 37) and Figure 3.27 (p. 37) , respectively.

3.10.1 Typical performance

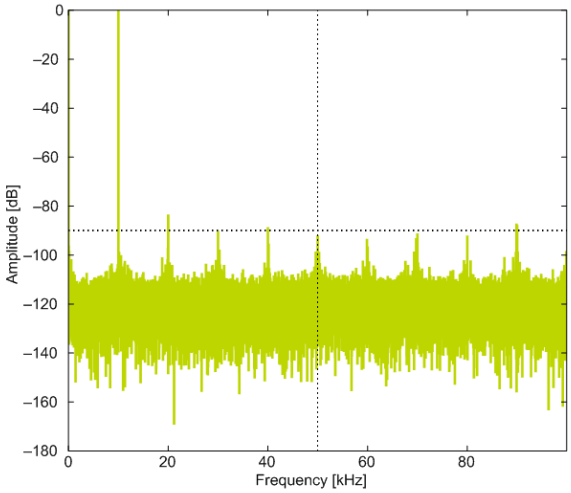
Figure 3.28. ADC Frequency Spectrum, Vdd = 3V, Temp = 25°C



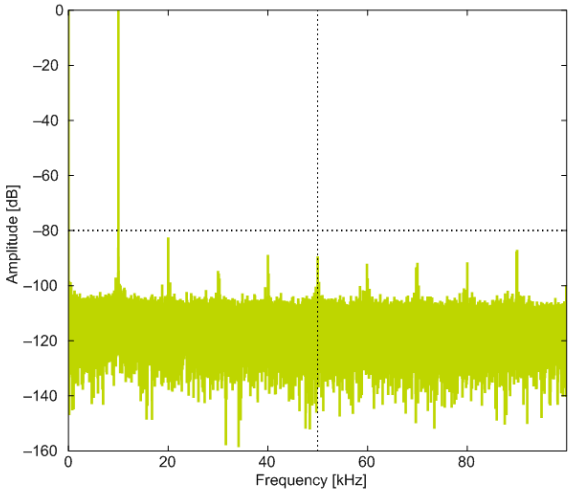
1.25V Reference



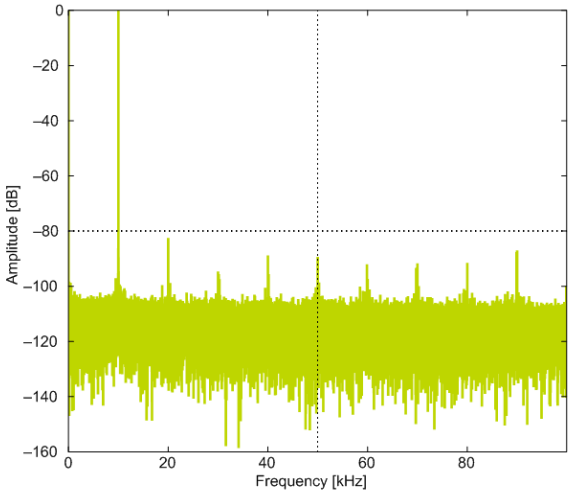
2.5V Reference



2XVDDVSS Reference

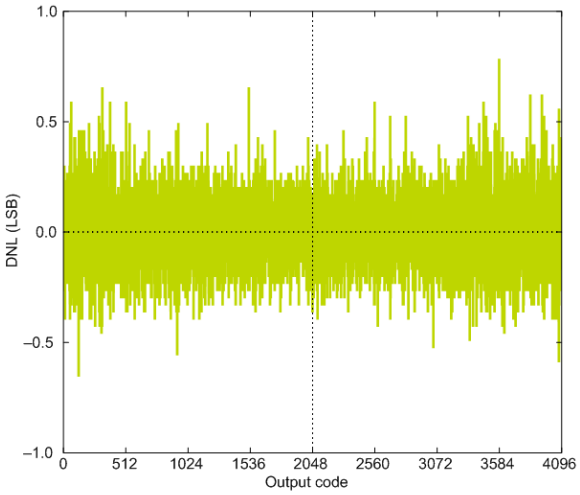


5VDIFF Reference

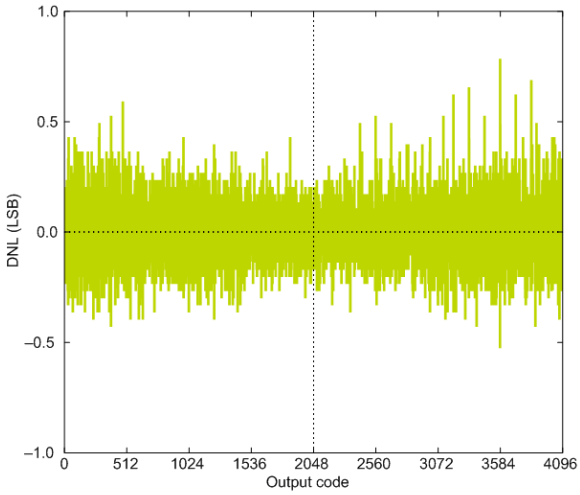


VDD Reference

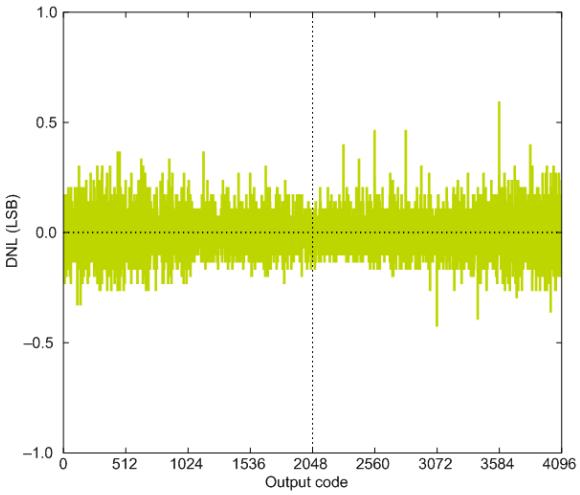
Figure 3.30. ADC Differential Linearity Error vs Code, Vdd = 3V, Temp = 25°C



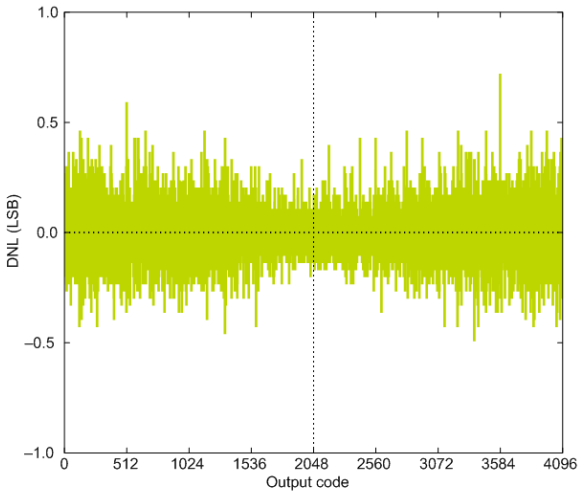
1.25V Reference



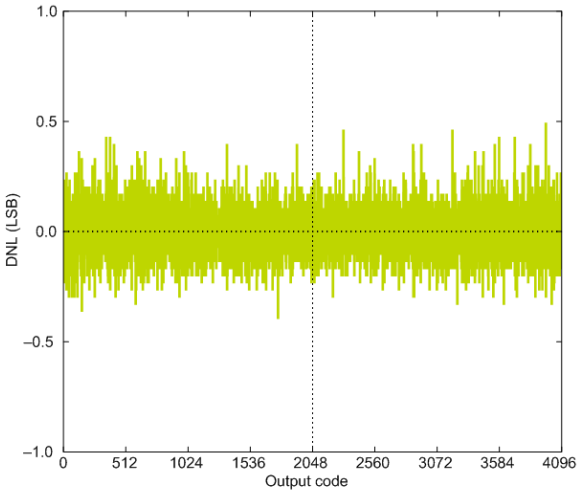
2.5V Reference



2XVDDVSS Reference

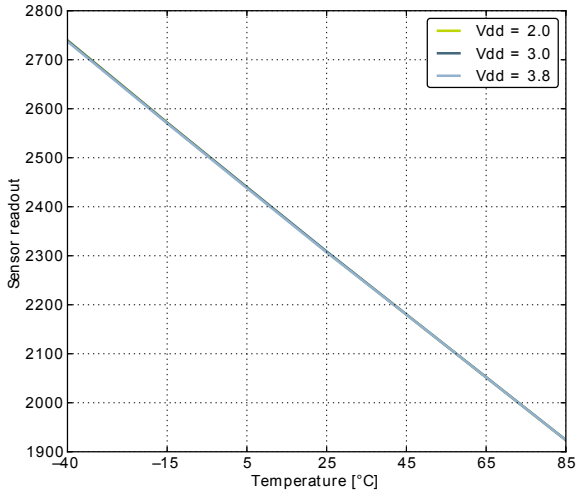


5VDIFF Reference



VDD Reference

Figure 3.33. ADC Temperature sensor readout



3.11 Current Digital Analog Converter (IDAC)

Table 3.16. IDAC Range 0 Source

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{IDAC}	Active current with STEPSEL=0x10	EM0, default settings		13.0		µA
		Duty-cycled		10		nA
I_{0x10}	Nominal IDAC output current with STEPSEL=0x10			0.85		µA
I_{STEP}	Step size			0.05		µA
I_D	Current drop at high impedance load	V_{IDAC_OUT} = V_{DD} - 100mV		0.79		%
TC_{IDAC}	Temperature coefficient	V_{DD} = 3.0V, STEPSEL=0x10		0.3		nA/°C
VC_{IDAC}	Voltage coefficient	T = 25 °C, STEPSEL=0x10		11.7		nA/V

Table 3.17. IDAC Range 0 Sink

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{IDAC}	Active current with STEPSEL=0x10	EM0, default settings		15.1		µA
I_{0x10}	Nominal IDAC output current with STEPSEL=0x10			0.85		µA
I_{STEP}	Step size			0.05		µA
I_D	Current drop at high impedance load	V_{IDAC_OUT} = 200 mV		0.30		%
TC_{IDAC}	Temperature coefficient	V_{DD} = 3.0 V, STEPSEL=0x10		0.2		nA/°C
VC_{IDAC}	Voltage coefficient	T = 25 °C, STEPSEL=0x10		12.5		nA/V

Table 3.18. IDAC Range 1 Source

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{IDAC}	Active current with STEPSEL=0x10	EM0, default settings		14.4		µA
		Duty-cycled		10		nA
I_{0x10}	Nominal IDAC output current with STEPSEL=0x10			3.2		µA
I_{STEP}	Step size			0.1		µA
I_D	Current drop at high impedance load	V_{IDAC_OUT} = V_{DD} - 100mV		0.75		%
TC_{IDAC}	Temperature coefficient	V_{DD} = 3.0 V, STEPSEL=0x10		0.7		nA/°C
VC_{IDAC}	Voltage coefficient	T = 25 °C, STEPSEL=0x10		38.4		nA/V

Table 3.19. IDAC Range 1 Sink

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{IDAC}	Active current with STEPSEL=0x10	EM0, default settings		19.4		µA
I_{0x10}	Nominal IDAC output current with STEPSEL=0x10			3.2		µA
I_{STEP}	Step size			0.1		µA
I_D	Current drop at high impedance load	V_{IDAC_OUT} = 200 mV		0.32		%
TC_{IDAC}	Temperature coefficient	V_{DD} = 3.0 V, STEPSEL=0x10		0.7		nA/°C
VC_{IDAC}	Voltage coefficient	T = 25 °C, STEPSEL=0x10		40.9		nA/V

Table 3.20. IDAC Range 2 Source

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{IDAC}	Active current with STEPSEL=0x10	EM0, default settings		17.3		µA
		Duty-cycled		10		nA
I_{0x10}	Nominal IDAC output current with STEPSEL=0x10			8.5		µA
I_{STEP}	Step size			0.5		µA
I_D	Current drop at high impedance load	V_{IDAC_OUT} = V_{DD} - 100mV		1.22		%
TC_{IDAC}	Temperature coefficient	V_{DD} = 3.0 V, STEPSEL=0x10		2.8		nA/°C
VC_{IDAC}	Voltage coefficient	T = 25 °C, STEPSEL=0x10		96.6		nA/V

Table 3.21. IDAC Range 2 Sink

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{IDAC}	Active current with STEPSEL=0x10	EM0, default settings		29.3		µA

4 Pinout and Package

Note

Please refer to the application note "AN0002 EFM32 Hardware Design Considerations" for guidelines on designing Printed Circuit Boards (PCB's) for the EFM32HG222.

4.1 Pinout

The *EFM32HG222* pinout is shown in Figure 4.1 (p. 52) and Table 4.1 (p. 52). Alternate locations are denoted by "#" followed by the location number (Multiple locations on the same pin are split with "/"). Alternate locations can be configured in the LOCATION bitfield in the *_ROUTE register in the module in question.

Figure 4.1. EFM32HG222 Pinout (top view, not to scale)

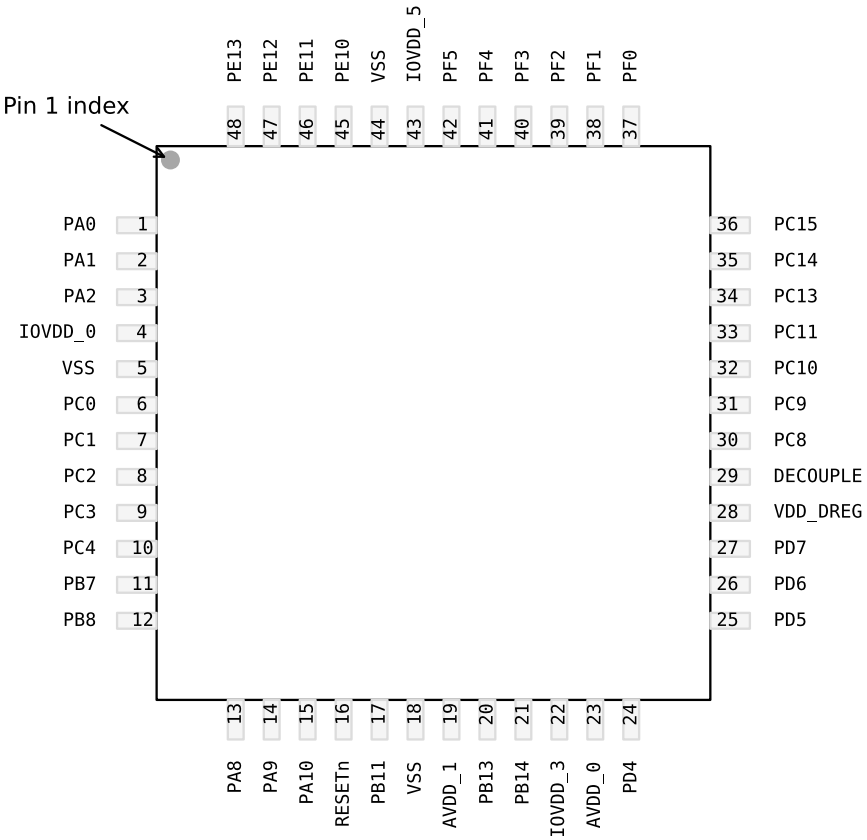


Table 4.1. Device Pinout

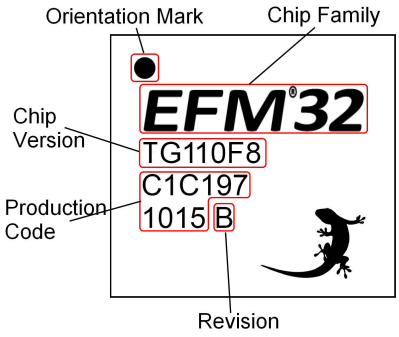
QFP48 Pin# and Name		Pin Alternate Functionality / Description			
Pin #	Pin Name	Analog	Timers	Communication	Other
1	PA0		TIM0_CC1 #6 TIM0_CC0 #0/1/4 PCNT0_S0IN #4	US1_RX #4 LEU0_RX #4 I2C0_SDA #0	PRS_CH0 #0 PRS_CH3 #3 GPIO_EM4WU0
2	PA1		TIM0_CC0 #6 TIM0_CC1 #0/1	I2C0_SCL #0	CMU_CLK1 #0 PRS_CH1 #0

6 Chip Marking, Revision and Errata

6.1 Chip Marking

In the illustration below package fields and position are shown.

Figure 6.1. Example Chip Marking (top view)



6.2 Revision

The revision of a chip can be determined from the "Revision" field in Figure 6.1 (p. 62) .

6.3 Errata

Please see the errata document for EFM32HG222 for description and resolution of device erratas. This document is available in Simplicity Studio and online at:
http://www.silabs.com/support/pages/document-library.aspx?p=MCUs--32-bit

7 Revision History

7.1 Revision 1.00

December 4th, 2015

Updated all specs with results of full characterization.

Updated part number to revision B.

7.2 Revision 0.91

May 6th, 2015

Updated current consumption table for energy modes.

Updated GPIO max leakage current.

Updated startup time for HFXO and LFXO.

Updated current consumption for HFRCO and LFRCO.

Updated ADC current consumption.

Updated IDAC characteristics tables.

Updated ACMP internal resistance.

Updated VCMP current consumption.

7.3 Revision 0.90

March 16th, 2015

Note

This datasheet revision applies to a product under development. It's characteristics and specifications are subject to change without notice.

Corrected EM2 current consumption condition in Electrical Characteristics section.

Updated GPIO electrical characteristics.

Updated Max ESR_{HFXO} value for Crystal Frequency of 25 MHz.

Updated LFRCO plots.

Updated HFRCO table and plots.

Updated ADC table and temp sensor plot.

Added DMA current in Digital Peripherals section.

Updated block diagram.

Corrected leadframe type to matte-Sn.

7.4 Revision 0.20

December 11th, 2014

B Contact Information

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Please visit the Silicon Labs Technical Support web page:
http://www.silabs.com/support/pages/contacttechnicalsupport.aspx
and register to submit a technical support request.

List of Figures

List of Equations